

30A, 400V - 600V Ultrafast Dual Diodes

RURH3040CC and RURH3060CC are ultrafast dual diodes ($t_{rr} < 55\text{ns}$) with soft recovery characteristics. They have a low forward voltage drop and are of planar, silicon nitride passivated, ion-implanted, epitaxial construction.

These devices are intended for use as energy steering/clamping diodes and rectifiers in a variety of switching power supplies and other power switching applications. Their low stored charge and ultrafast recovery with soft recovery characteristics minimize ringing and electrical noise in many power switching circuits, thus reducing power loss in the switching transistor.

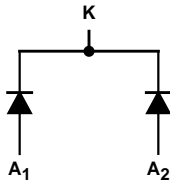
Formerly developmental type TA09903.

Ordering Information

PART NUMBER	PACKAGE	BRAND
RURH3040CC	TO-218AC	RURH3040C
RURH3060CC	TO-218AC	RURH3060C

NOTE: When ordering, use the entire part number.

Symbol



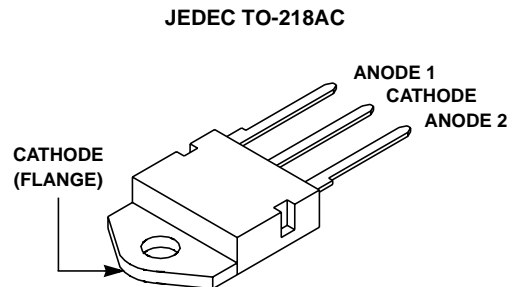
Features

- Ultrafast with Soft Recovery 55ns
- Operating Temperature 175°C
- Reverse Voltage Up to 600V
- Avalanche Energy Rated
- Planar Construction

Applications

- Switching Power Supply
- Power Switching Circuits
- General Purpose

Packaging



Absolute Maximum Ratings (Per Leg) $T_C = 25^{\circ}\text{C}$, Unless Otherwise Specified

	RURH3040CC	RURH3060CC	UNITS
Peak Repetitive Reverse Voltage.....	V_{RRM} 400	600	V
Working Peak Reverse Voltage.....	V_{RWM} 400	600	V
DC Blocking Voltage.....	V_R 400	600	V
Average Rectified Forward Current..... ($T_C = 130^{\circ}\text{C}$)	$I_{F(AV)}$ 30	30	A
Repetitive Peak Surge Current..... (Square Wave 20kHz)	I_{FRM} 70	70	A
Nonrepetitive Peak Surge Current..... (Halfwave 1 Phase 60Hz)	I_{FSM} 325	325	A
Maximum Power Dissipation.....	P_D 125	125	W
Avalanche Energy (See Figures 7 and 8).....	E_{VAL} 20	20	mJ
Operating and Storage Temperature.....	T_{STG}, T_J -55 to 175	-55 to 175	$^{\circ}\text{C}$

RURH3040CC, RURH3060CC

Electrical Specifications (Per Leg) $T_C = 25^\circ\text{C}$, Unless Otherwise Specified

SYMBOL	TEST CONDITION	MIN	TYP	MAX	MIN	TYP	MAX	UNITS
V_F	$I_F = 30\text{A}$	-	-	1.5	-	-	1.5	V
	$I_F = 30\text{A}, T_C = 150^\circ\text{C}$	-	-	1.3	-	-	1.3	V
I_R	$V_R = 400\text{V}$	-	-	250	-	-	-	μA
	$V_R = 600\text{V}$	-	-	-	-	-	250	μA
	$V_R = 400\text{V}, T_C = 150^\circ\text{C}$	-	-	1	-	-	-	mA
	$V_R = 600\text{V}, T_C = 150^\circ\text{C}$	-	-	-	-	-	1	mA
t_{rr}	$I_F = 1\text{A}, dI_F/dt = 100\text{A}/\mu\text{s}$	-	-	55	-	-	55	ns
	$I_F = 30\text{A}, dI_F/dt = 100\text{A}/\mu\text{s}$	-	-	60	-	-	60	ns
t_a	$I_F = 30\text{A}, dI_F/dt = 100\text{A}/\mu\text{s}$	-	30	-	-	30	-	ns
t_b	$I_F = 30\text{A}, dI_F/dt = 100\text{A}/\mu\text{s}$	-	20	-	-	20	-	ns
$R_{\theta JC}$		-	-	1.2	-	-	1.2	$^\circ\text{C}/\text{W}$

DEFINITIONS

V_F = Instantaneous forward voltage (pw = 300 μs , D = 2%).

I_R = Instantaneous reverse current.

t_{rr} = Reverse recovery time at $dI_F/dt = 100\text{A}/\mu\text{s}$ (See Figure 6), summation of $t_a + t_b$.

t_a = Time to reach peak reverse current at $dI_F/dt = 100\text{A}/\mu\text{s}$ (See Figure 6).

t_b = Time from peak I_{RM} to projected zero crossing of I_{RM} based on a straight line from peak I_{RM} through 25% of I_{RM} (See Figure 6).

$R_{\theta JC}$ = Thermal resistance junction to case.

pw = Pulse width.

D = Duty cycle.

Typical Performance Curves

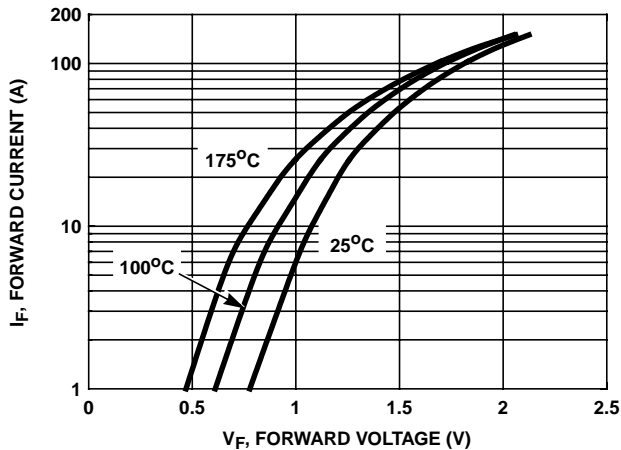


FIGURE 1. FORWARD CURRENT vs FORWARD VOLTAGE

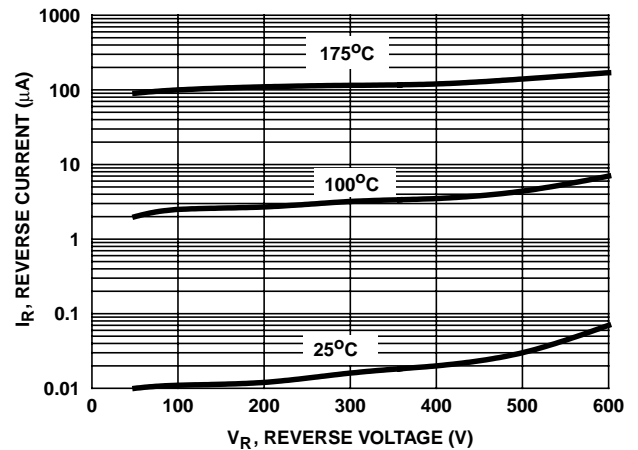


FIGURE 2. REVERSE CURRENT vs REVERSE VOLTAGE

Typical Performance Curves (Continued)

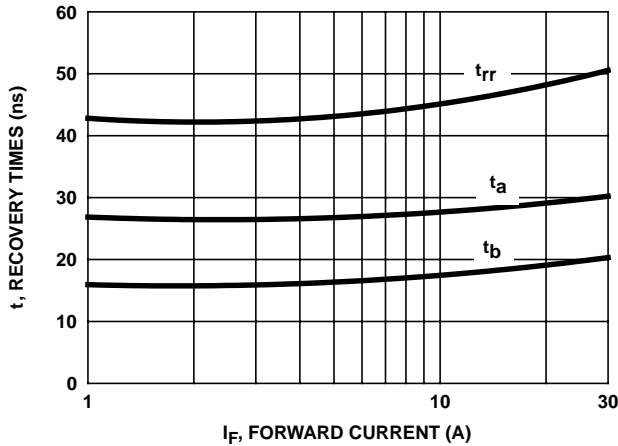


FIGURE 3. t_{rr} , t_a AND t_b CURVES vs FORWARD CURRENT

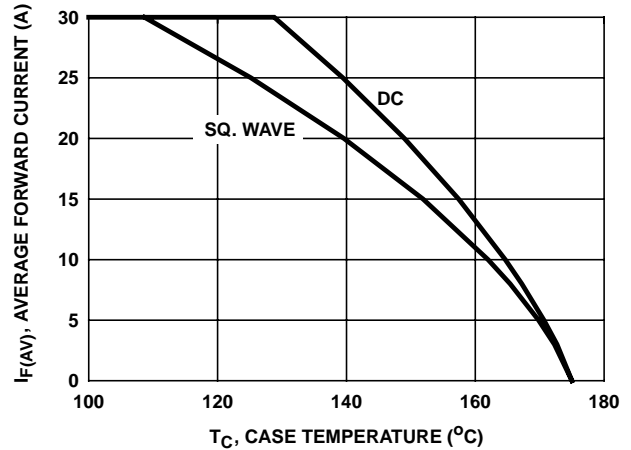


FIGURE 4. CURRENT DERATING CURVE

Test Circuits and Waveforms

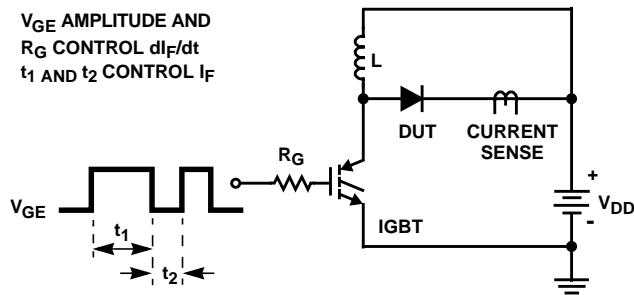


FIGURE 5. t_{rr} TEST CIRCUIT

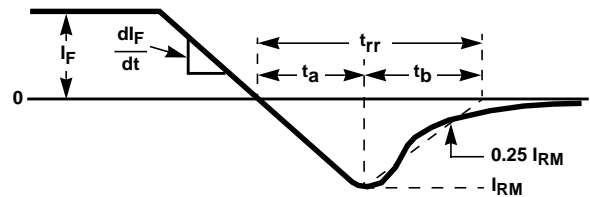


FIGURE 6. t_{rr} WAVEFORMS AND DEFINITIONS

$I = 1A$
 $L = 40mH$
 $R < 0.1\Omega$
 $E_{AVL} = 1/2LI^2 [V_{R(AVL)}/(V_{R(AVL)} - V_{DD})]$
 $Q_1 = IGBT (BV_{CES} > DUT V_{R(AVL)})$

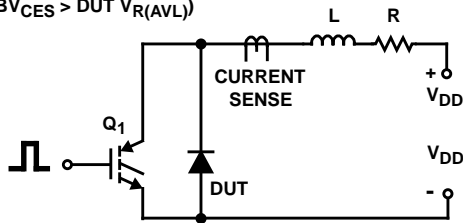


FIGURE 7. AVALANCHE ENERGY TEST CIRCUIT

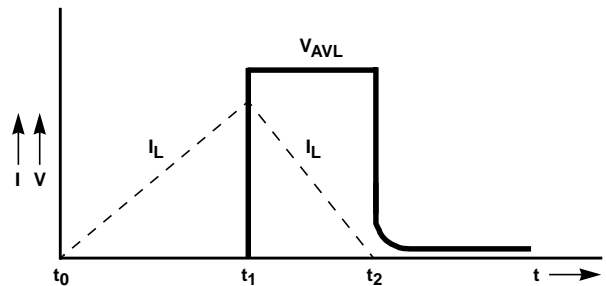


FIGURE 8. AVALANCHE CURRENT AND VOLTAGE WAVEFORMS

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